

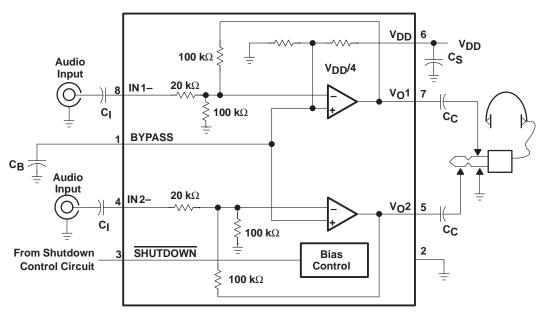
description

The TPA6102A2 is a stereo audio power amplifier packaged in either an 8-pin SOIC package or an 8-pin MOSP package capable of delivering 50 mW of continuous RMS power per channel into 16- Ω loads. Amplifier gain is internally set to 14 dB (inverting) to save board space by eliminating 6 external resistors.

The TPA6102A2 is optimized for battery applications because of its low supply current, shutdown current, and THD+N. To obtain the low supply voltage range, the TPA6102A2 biases BYPASS to V_{DD}/4.

When driving a $16-\Omega$ load with 40 mW output power from 3.3 V, THD+N is 0.08% at 1 kHz, and less than 0.2% across the audio band of 20 Hz to 20 kHz. For 30 mW into $32-\Omega$ loads, the THD+N is reduced to less than 0.06% at 1 kHz, and is less than 0.3% across the audio band of 20 Hz to 20 kHz.

typical application circuit





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



AVAILABLE OPTIONS

т.	PACKAGE	MSOP	
'A	SMALL OUTLINE (D)	SYMBOLIZATION	
-40°C to 85°C	TPA6102A2D	TPA6102A2DGK	AJN

Terminal Functions

TERMINAL		1/0	DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
BYPASS	1	I	Tap to voltage divider for internal mid-supply bias supply. BYPASS is set at $V_{DD}/4$. Connect to a 0.1 μ F to 1 μ F low ESR capacitor for best performance.
GND	2	I	GND is the ground connection.
IN1-	8	Ι	IN1– is the inverting input for channel 1.
IN2-	4	-1	IN2– is the inverting input for channel 2.
SHUTDOWN	3	-1	Active-low input. When held low, the device is placed in a low supply current mode.
V_{DD}	6	Ι	V _{DD} is the supply voltage terminal.
V _O 1	7	0	V _O 1 is the audio output for channel 1.
V _O 2	5	0	V _O 2 is the audio output for channel 2.

absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage, V _{DD}	4 V
Input voltage, V _I	\dots -0.3 V to V _{DD} + 0.3 V
Continuous total power dissipation	Internally Limited
Operating junction temperature range, T _J	
Storage temperature range, T _{stq}	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{\scriptsize A}} \le 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING
D	710 mW	5.68 mW/°C	454 mW	369 mW
DGK	469 mW	3.75 mW/°C	300 mW	244 mW

recommended operating conditions

	MIN	MAX	UNIT
Supply voltage, V _{DD}	1.6	3.6	V
Operating free-air temperature, T _A	-40	85	°C



dc electrical characteristics at T_A = 25°C, V_{DD} = 3.3 V

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
PSRR	Power supply rejection ratio	V _{DD} = 3 V to 3.6 V		72		dB
I _{DD}	Supply current			0.75	1.2	mA
I _{DD(SD)}	Supply current in SHUTDOWN mode			50	250	nA
IIIII	High-level input current (SHUTDOWN)	$V_{DD} = 3.3 \text{ V}, V_{I} = V_{DD}$			1	μΑ
I _I L	Low-level input current (SHUTDOWN)	$V_{DD} = 3.3 \text{ V}, V_{I} = 0 \text{ V}$			1	μΑ
Z _l	Input impedance			20		kΩ

ac operating characteristics, $\rm V_{DD}$ = 3.3 V, $\rm T_A$ = 25°C, $\rm R_L$ = 16 Ω

	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
G	Gain		14	dB
PO	Output power (each channel)	THD \leq 0.1%, f = 1 kHz	50	mW
THD+N	Total harmonic distortion + noise	$P_0 = 45 \text{ mW}, 20-20 \text{ kHz}$	0.4%	
Вом	Maximum output power BW	THD < 0.5%	> 20	kHz
ksvr	Supply ripple rejection	f = 1 kHz	47	dB
SNR	Signal-to-noise ratio	P _O = 50 mW	86	dB
٧n	Noise output voltage (no noise weighting filter)		45	μV(rms)

ac operating characteristics, $\rm V_{DD}$ = 3.3 V, $\rm T_A$ = 25°C, $\rm R_L$ = 32 Ω

	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
G	Gain		14	dB
PO	Output power (each channel)	THD ≤ 0.1%, f = 1 kHz	35	mW
THD+N	Total harmonic distortion + noise	$P_0 = 30 \text{ mW}, 20-20 \text{ kHz}$	0.4%	
ВОМ	Maximum output power BW	THD < 0.4%	>20	kHz
ksvr	Supply ripple rejection	f = 1 kHz	47	dB
SNR	Signal-to-noise ratio	P _O = 30 mW	86	dB
Vn	Noise output voltage (no noise weighting filter)		50	μV(rms)

TPA6102A2 50-mW FIXED-GAIN STEREO AUDIO POWER AMPLIFIER

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dc electrical characteristics at T_A = 25°C, V_{DD} = 1.6 V

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
PSRR	Power supply rejection ratio	V _{DD} = 1.4 V to 1.8 V		80		dB
I _{DD}	Supply current			0.65	1.2	mA
I _{DD} (SD)	Supply current in SHUTDOWN mode			50	250	nA
IIIII	High-level input current (SHUTDOWN)	$V_{DD} = 1.6 \text{ V}, V_{I} = V_{DD}$			1	μΑ
I _I L	Low-level input current (SHUTDOWN)	$V_{DD} = 1.6 \text{ V}, V_{I} = 0 \text{ V}$			1	μΑ
Z _l	Input impedance			20		kΩ

ac operating characteristics, $\rm V_{DD}$ = 1.6 V, $\rm T_A$ = 25°C, $\rm R_L$ = 16 Ω

	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
G	Gain		14	dB
PO	Output power (each channel)	THD \leq 0.5%, f = 1 kHz	10	mW
THD+N	Total harmonic distortion + noise	$P_0 = 9.5 \text{ mW}, 20-20 \text{ kHz}$	0.06%	
ВОМ	Maximum output power BW	THD < 1%	> 20	kHz
ksvr	Supply ripple rejection	f = 1 kHz	47	dB
SNR	Signal-to-noise ratio	P _O = 10 mW	82	dB
٧n	Noise output voltage (no noise weighting filter)		32	μV(rms)

ac operating characteristics, $\rm V_{DD}$ = 1.6 V, $\rm T_A$ = 25°C, $\rm R_L$ = 32 Ω

	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
G	Gain		14	dB
PO	Output power (each channel)	THD ≤ 0.5%, f = 1 kHz	7.5	mW
THD+N	Total harmonic distortion + noise	$P_O = 6.5 \text{ mW}, 20-20 \text{ kHz}$	0.05%	
ВОМ	Maximum output power BW	THD < 1%	>20	kHz
ksvr	Supply ripple rejection	f = 1 kHz	47	dB
SNR	Signal-to-noise ratio	P _O = 7.5 mW	84	dB
Vn	Noise output voltage (no noise weighting filter)		32	μV(rms)

APPLICATION INFORMATION

input capacitor, CI

In the typical application, an input capacitor, C_I , is required to allow the amplifier to bias the input signal to the proper dc level for optimum operation. In this case, C_I and R_I form a high-pass filter with the corner frequency determined in equation 1. R_I is set internally and is fixed at 20 k Ω .

$$f_{C} = \frac{1}{2\pi R_{I}C_{I}} \tag{1}$$

The value of C_l is important to consider, as it directly affects the bass (low frequency) performance of the circuit. Consider the example where the specification calls for a flat bass response down to 20 Hz. Equation 1 is reconfigured as equation 2.

$$C_{I} = \frac{1}{2\pi R_{I} f_{C}}$$
 (2)

In this example, C_I is 0.40 μ F, so one would likely choose a value in the range of 0.47 μ F to 1 μ F. A further consideration for this capacitor is the leakage path from the input source through the input network (R_I , C_I) and the feedback resistor (R_F) to the load. This leakage current creates a dc offset voltage at the input to the amplifier that reduces useful headroom. For this reason a low-leakage tantalum or ceramic capacitor is the best choice. When polarized capacitors are used, the positive side of the capacitor should face the amplifier input in most applications, as the dc level there is held at $V_{DD}/4$, which is likely higher than the source dc level. It is important to confirm the capacitor polarity in the application.

power supply decoupling, CS

The TPA6102A2 is a high-performance CMOS audio amplifier that requires adequate power supply decoupling to ensure that the output total harmonic distortion (THD) is as low as possible. Power supply decoupling also prevents oscillations for long lead lengths between the amplifier and the speaker. The optimum decoupling is achieved by using two capacitors of different types that target different types of noise on the power supply leads. For higher frequency transients, spikes, or digital hash on the line, a good low equivalent-series-resistance (ESR) ceramic capacitor, typically 0.1 μ F, placed as close as possible to the device V_{DD} lead, works best. For filtering lower-frequency noise signals, a larger aluminum electrolytic capacitor of 10 μ F or greater placed near the power amplifier is recommended.

midrail bypass capacitor, CB

The midrail bypass capacitor, C_B , serves several important functions. During startup, C_B determines the rate at which the amplifier starts up. This helps to push the start-up pop noise into the subaudible range (so low it can not be heard). The second function is to reduce noise produced by the power supply caused by coupling into the output drive signal. This noise is from the midrail generation circuit internal to the amplifier. The capacitor is fed from a 55-k Ω source inside the amplifier. To keep the start-up pop as low as possible, the relationship shown in equation 3 should be maintained.

$$\frac{1}{\left(C_{\mathsf{B}} \times 55 \text{ k}\Omega\right)} \le \frac{1}{\left(C_{\mathsf{I}}\mathsf{R}_{\mathsf{I}}\right)} \tag{3}$$

As an example, consider a circuit where C_B is 1 μ F, C_I is 1 μ F, and R_I is 20 $k\Omega$. Inserting these values into the equation 3 results in: 18.18 \leq 50 which satisfies the rule. Bypass capacitor, C_B , values of 0.47 μ F to 1 μ F ceramic or tantalum low-ESR capacitors are recommended for the best THD and noise performance.



APPLICATION INFORMATION

output coupling capacitor, CC

In the typical single-supply single-ended (SE) configuration, an output coupling capacitor (C_C) is required to block the dc bias at the output of the amplifier, thus preventing dc currents in the load. As with the input coupling capacitor, the output coupling capacitor and impedance of the load form a high-pass filter governed by equation 4.

$$f_{C} = \frac{1}{2\pi R_{L} C_{C}} \tag{4}$$

The main disadvantage, from a performance standpoint, is that the typically small load impedances drive the low-frequency corner higher. Large values of C_C are required to pass low frequencies into the load. Consider the example where a C_C of 68 μF is chosen and loads vary from 32 Ω to 47 $k\Omega$. Table 1 summarizes the frequency response characteristics of each configuration.

Table 1. Common Load Impedances Vs Low Frequency Output Characteristics in SE Mode

RL	СС	Lowest Frequency
32 Ω	68 μF	73 Hz
10,000 Ω	68 μF	0.23 Hz
47,000 Ω	68 μF	0.05 Hz

As Table 1 indicates, headphone response is adequate and drive into line level inputs (a home stereo for example) is very good.

The output coupling capacitor required in single-supply SE mode also places additional constraints on the selection of other components in the amplifier circuit. With the rules described earlier still valid, add the following relationship:

$$\frac{1}{\left(\mathsf{C}_{\mathsf{B}} \times 55 \ \mathsf{k}\Omega\right)} \le \frac{1}{\left(\mathsf{C}_{\mathsf{I}}\mathsf{R}_{\mathsf{I}}\right)} \ll \frac{1}{\mathsf{R}_{\mathsf{L}}\mathsf{C}_{\mathsf{C}}} \tag{5}$$

using low-ESR capacitors

Low-ESR capacitors are recommended throughout this application. A real capacitor can be modeled simply as a resistor in series with an ideal capacitor. The voltage drop across this resistor minimizes the beneficial effects of the capacitor in the circuit. The lower the equivalent value of this resistance, the more the real capacitor behaves like an ideal capacitor.

3.3-V versus 1.6-V operation

The TPA6102A2 was designed for operation over a supply range of 1.6 V to 3.6 V. There are no special considerations for 1.6-V versus 3.3-V operation as far as supply bypassing, gain setting, or stability. Supply current is slightly reduced from 0.75 mA (typical) to 0.65 mA (typical). The most important consideration is that of output power. Each amplifier can produce a maxium output voltage swing within a few hundred millivolts of the rails with a 10-k Ω load. However, this voltage swing decreases as the load resistance decreases and the rDS(on) as the output stage transistors becomes more significant. For example, for a 32- Ω load, the maximum peak output voltage with VDD = 1.6 V is approximately 0.7 V with no clipping distortion. This reduced voltage swing effectively reduces the maximum undistorted output power.

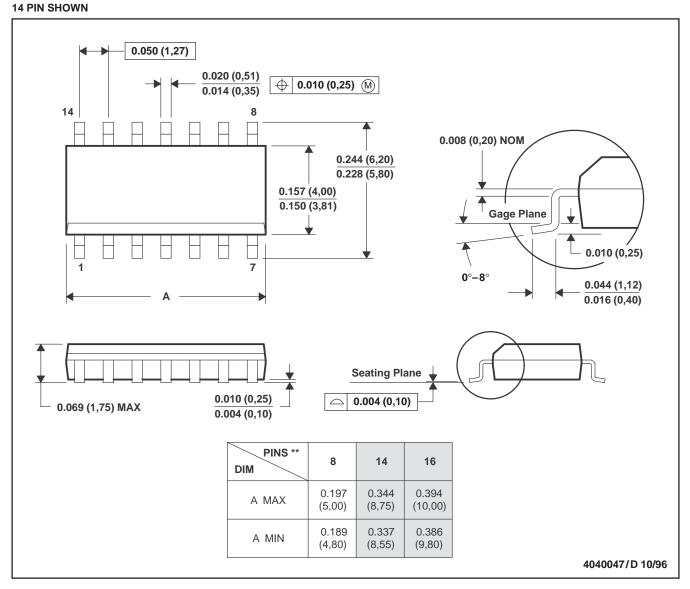


MECHANICAL DATA

D (R-PDSO-G**)

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PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

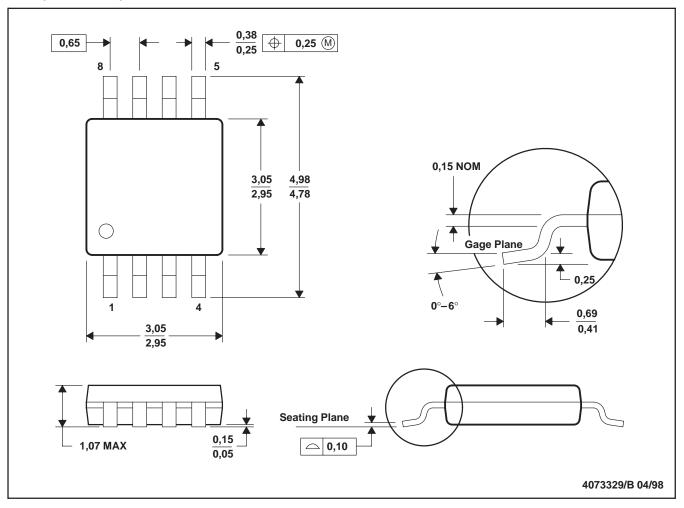
B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).

MECHANICAL INFORMATION

DGK (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion.

D. Falls within JEDEC MO-187

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